OXFORD INSTRUMENTS

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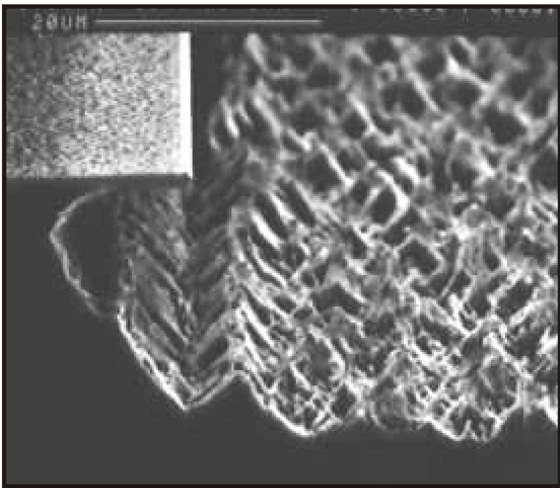
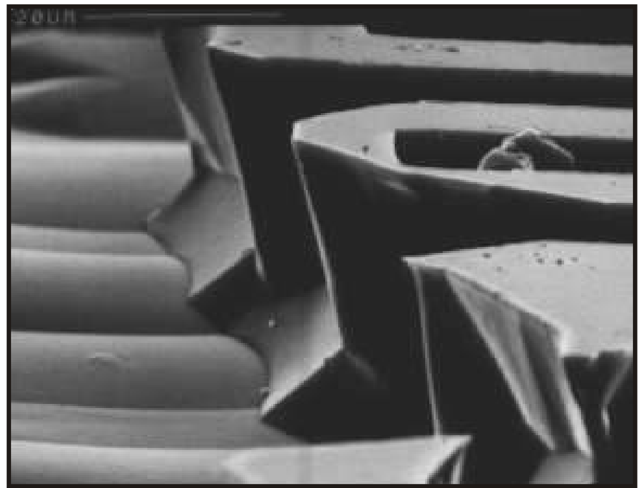
Plasmalab Data

GaAs Surface Roughening / Modification



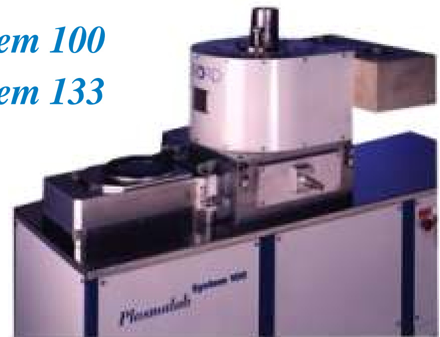


25 µm deep Etch through

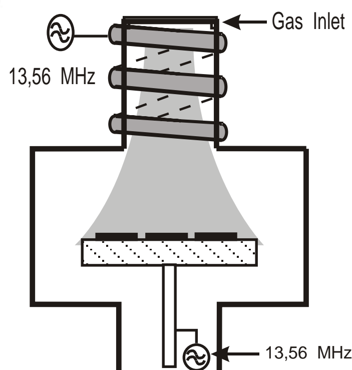
with controlled ion bombardment

without ion bombardment

Plasmalab System 100
Plasmalab System 133



Plasmalab 80 Plus



Technology:

Remote Downstream Plasma*
Source Power => Plasma Density
RF Power => Ion Energy

*original work by DSMW, see:
http://www.oxfordplasma.de/technols/rie_mwds.htm

Results:

Rate : 0.2 - 5 µm / min
Crystallographic etching without ion bombardment
Increasing roughness with increasing ion bombardment